Siliconix incorporated

TN2010L, TN2410L

N-Channel Enhancement-Mode MOS Transistors

T-35-25

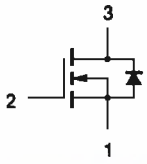
PRODUCT SUMMARY

PART NUMBER	$V_{(BR)DSS}$ (V)	$r_{DS(ON)}$ (Ω)	I_D (A)
TN2010L	200	10	0.18
TN2410L	240	10	0.18

Performance Curves: VNDB24

TO-92 (TO-226AA) BOTTOM VIEW

1 SOURCE
2 GATE
3 DRAIN



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS TN2010L	LIMITS TN2410L	UNITS
Drain-Source Voltage		V_{DS}	200	240	V
Gate-Source Voltage		V_{GS}	±20	±20	
Continuous Drain Current	T_A = 25°C	I_D	±0.18	±0.18	A
	T_A = 100°C		±0.11	±0.11	
Pulsed Drain Current[1]		I_{DM}	±1	±1	
Maximum Power Dissipation	T_A = 25°C	P_D	0.8	0.8	W
	T_A = 100°C		0.32	0.32	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	−55 to 150		°C
Lead Temperature ($^1/_{16}$" from case for 10 sec.)		T_L	300		

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	LIMITS	UNITS
Junction-to-Ambient	R_{thJA}	156	K/W

[1]Pulse width limited by maximum junction temperature.

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SPECIFICATIONS[a]				LIMITS			
PARAMETER	SYMBOL	TEST CONDITIONS		TYP[b]	MIN	MAX	UNIT
STATIC							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V	TN2410L	260	240		V
		I_D = 100 µA	TN2010L	240	200		
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 1 mA		1.4	0.5	1.8	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V		±1		±10	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 0.8 x rated $V_{(BR)DSS}$, V_{GS} = 0 V		0.01		1	µA
			T_J = 125°C	1.0		100	
On-State Drain Current[c]	$I_{D(ON)}$	V_{DS} = 10 V, V_{GS} = 4.5 V		0.8	0.25		A
Drain-Source On-Resitance[c]	$r_{DS(ON)}$	V_{GS} = 3.5 V, I_D = 50 mA		6		15	Ω
		V_{GS} = 4.5 V, I_D = 200 mA		5		10	
			T_J = 125°C	10		20	
Forward Transconductance[c]	g_{FS}	V_{DS} = 10 V, I_D = 0.2 A		500	100		mS
DYNAMIC							
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		110		135	pF
Output Capacitance	C_{oss}			30		50	
Reverse Transfer Capacitance	C_{rss}			5		20	
SWITCHING							
Turn-On Time	t_{ON}	V_{DD} = 60 V, R_L = 150 Ω, I_D = 0. 4 A V_{GEN} = 10 V, R_G = 25 Ω		15		35	ns
Turn-Off Time	t_{OFF}	(Switching time is essentially independent of operating temperature)		30		60	

NOTES:
a. T_A = 25°C unless otherwise noted.
b. For design aid only, not subject to production testing.
c. Pulse test: Pulse Width ≤ 300 µsec, Duty Cycle ≤ 2%.